

N-Channel Super Junction Power MOSFET III

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent R_{DS(ON)} with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

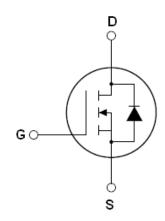
Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- ●Small package
- ●Ultra Low Gate Charge cause lower driving requirements
- ●100% Avalanche Tested
- ●ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

V _{DS} @T _{jmax}	650	V	
R _{DS(ON)} TYP	1.8	Ω	
I_D	2	A	



Schematic diagram

Package Marking And Ordering Information

Device	Device Package	Marking
NCE60T2K2I	TO-251	NCE60T2K2I
NCE60T2K2K	TO-252	NCE60T2K2K





TO-251

TO-252

Table 1. Absolute Maximum Ratings (T_c=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (VGS=0V)	V _{DS}	600	V
Gate-Source Voltage (V _{DS} =0V) ,AC (f>1 Hz)	V _{GS}	±30	V
Continuous Drain Current at Tc=25°C	I _{D (DC)}	2	А
Continuous Drain Current at Tc=100°C	I _{D (DC)}	1.25	Α
Pulsed drain current (Note 1)	I _{DM (pluse)}	8	Α
Maximum Power Dissipation(Tc=25℃)	P _D	21	W
Derate above 25°C		0.168	W/°C
Single pulse avalanche energy (Note2)	Eas	12	mJ
Avalanche current ^(Note 1)	I _{AR}	0.3	Α
Repetitive Avalanche energy , t_{AR} limited by T_{jmax} (Note 1)	E _{AR}	0.06	mJ



Parameter	Symbol	Value	Unit
Drain Source voltage slope, V _{DS} ≤480 V,	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS} \leq 480 \text{ V}, I_{SD} < I_{D}$	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55+150	°C

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R _{thJC}	5.95	°C /W
Thermal Resistance, Junction-to-Ambient (Maximum)	R _{thJA}	75	°C /W

Table 3. Electrical Characteristics (TA=25°Cunless otherwise noted)

Table 3. Liectifical Characteristics	cs (TA-23 Curiless otherwise noted)					
Parameter	Symbol	Condition	Min	Тур	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	600			V
Zero Gate Voltage Drain Current(Tc=25°C)	I _{DSS}	V _{DS} =600V,V _{GS} =0V			1	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I _{DSS}	V _{DS} =600V,V _{GS} =0V			10	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=70\mu A$	3	3.5	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =1A		1800	2200	mΩ
Dynamic Characteristics						
Input Capacitance	C _{Iss}	\/ -E0\/\/ -0\/		120		PF
Output Capacitance	Coss	V_{DS} =50V, V_{GS} =0V, F=1.0MHz		8		PF
Reverse Transfer Capacitance	C _{rss}	F-1.UIVITZ		0.2		PF
Total Gate Charge	Qg	\/ -400\/ -24		3.5	10	nC
Gate-Source Charge	Q _{gs}	V_{DS} =480V, I_{D} =2A, V_{GS} =10V		0.9		nC
Gate-Drain Charge	Q_{gd}	V _{GS} -10V		1.8		nC
Switching times						
Turn-on Delay Time	t _{d(on)}			10		nS
Turn-on Rise Time	t _r	V_{DD} =380V, I_{D} =1A,		9		nS
Turn-Off Delay Time	t _{d(off)}	R_G =10 Ω , V_{GS} =10 V		56		nS
Turn-Off Fall Time	t _f			11		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I _{SD}	T -25°C			2	Α
Pulsed Source-drain current(Body Diode)	I _{SDM}	T _C =25°C			8	Α
Forward On Voltage	V _{SD}	Tj=25°C,I _{SD} =2A,V _{GS} =0V		1	1.3	V
Reverse Recovery Time	t _{rr}			170		nS
Reverse Recovery Charge	Q _{rr}	Tj=25°C,I _F =1A,di/dt=100A/μs		0.26		uC
Peak reverse recovery current	I _{rrm}			3		Α
		·				

Notes: 1.Repetitive Rating: Pulse width limited by maximum junction temperature

^{2.} Tj=25°C,VDD=50V,VG=10V, R_G=25 Ω



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure 1. Safe operating area

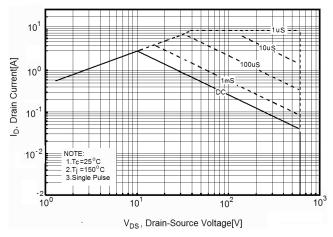


Figure 3. Output characteristics

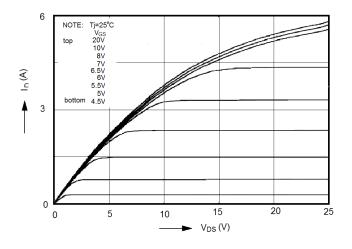


Figure 5. Static drain-source on resistance

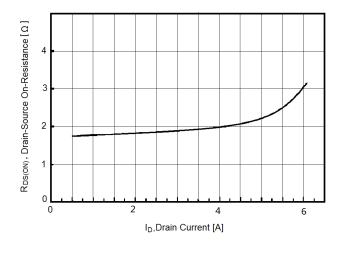


Figure2. Source-Drain Diode Forward Voltage

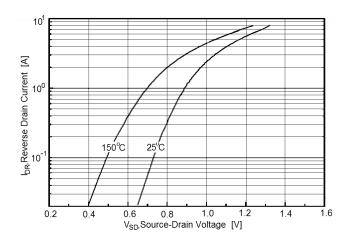


Figure 4. Transfer characteristics

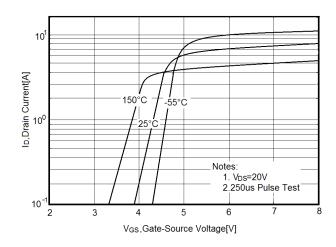


Figure 6. R_{DS(ON)} vs Junction Temperature

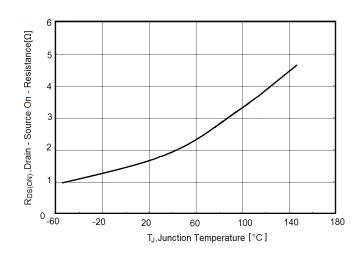




Figure 7. BV_{DSS} vs Junction Temperature

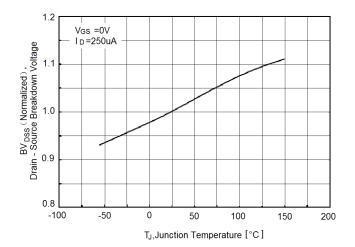


Figure 8. Maximum I_D vs Junction Temperature

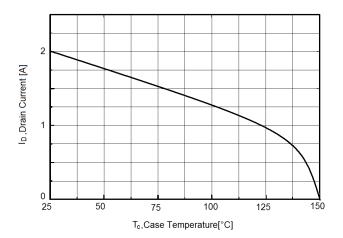
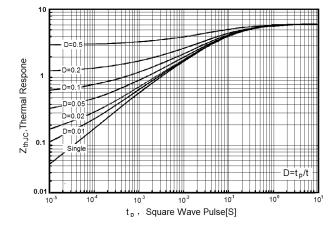


Figure 9. Transient Thermal Impedance

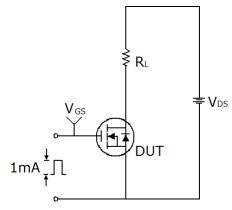


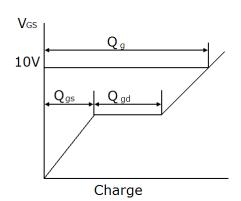




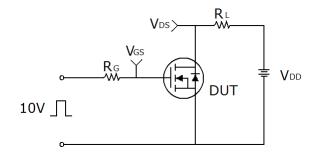
Test circuit

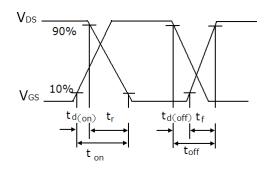
1) Gate charge test circuit & Waveform



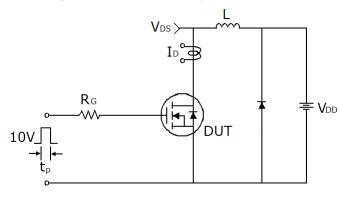


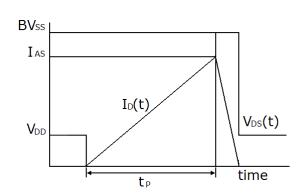
2) Switch Time Test Circuit:





3) Unclamped Inductive Switching Test Circuit & Waveforms

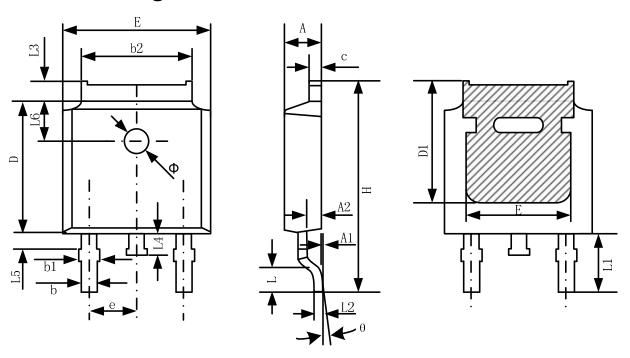








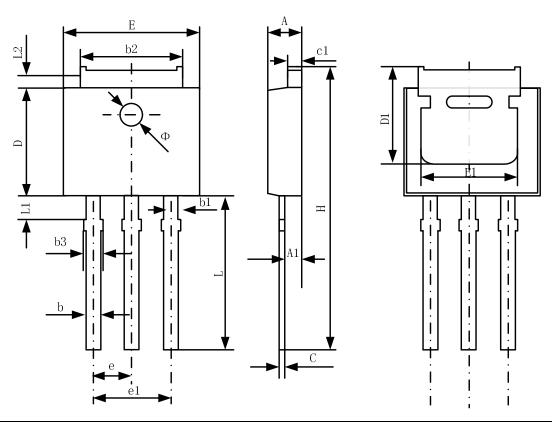
TO-252-2 Package Information



Ob. a.l.	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.20	2.38	0.087	0.094	
A1	0.00	0.10	0.000	0.004	
A2	0.90	1.10	0.035	0.043	
b	0.72	0.85	0.028	0.033	
b1	0.72	0.90	0.028	0.035	
b2	5.13	5.46	0.202	0.215	
С	0.47	0.60	0.019	0.024	
D	6.00	6.20	0.236	0.244	
D1	5.25		0.207		
E	6.50	6.70	0.256	0.264	
E1	4.70		0.185		
e	2.19	2.39	0.086	0.094	
Н	9.80	10.40	0.386	0.409	
L	1.40	1.70	0.055	0.067	
L1	2.90 REF		0.114 REF		
L2	0.508 BSC		0.020 BSC		
L3	0.90	1.25	0.035	0.049	
L4	0.60	1.00	0.024	0.039	
L5	0.15	0.75	0.006	0.030	
L6	1.80 REF		0.071 REF		
Ф	1.20	1.40	0.047	0.055	
θ	0°	8°	0°	8°	



TO-251 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	2.20	2.35	0.087	0.093	
A1	0.90	1.10	0.035	0.043	
b	0.56	0.69	0.022	0.027	
b1	0.77	0.90	0.030	0.035	
b2	5.23	5.43	0.206	0.214	
b3		1.05	0.000	0.041	
С	0.46	0.59	0.018	0.023	
c1	0.46	0.59	0.018	0.023	
D	6.00	6.20	0.236	0.244	
D1	5.20		0.205		
Е	6.50	6.70	0.256	0.264	
E1	4.60	5.00	0.181		
e	2.24	2.34	0.088	0.092	
e1	4.47	4.67	0.176	0.184	
Н	16.18	16.78	0.637	0.661	
L	9.00	9.60	0.354	0.378	
L1	0.95	1.35	0.037	0.053	
L2	0.90	1.25	0.035	0.049	

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NCE60T2K2I, NCE60T2K2K

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